

SANYO	No.2749	<h1 style="margin: 0;">2SK1069</h1> <p style="margin: 0;">N-Channel Junction Silicon FET</p> <p style="margin: 0;">Low-Frequency</p> <p style="margin: 0;">General-Purpose Amp Applications</p>
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Applications

- Low-frequency general-purpose amplifiers
- Ideal for use in variable resistors, analog switches, low-frequency amplifiers, and constant-current circuits

Features

- Adoption of FBET process
- Very small-sized package permitting 2SK1069-applied sets to be made smaller and slimmer

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V _{DSX}	40	V
Gate to Drain Voltage	V _{GD}	-40	V
Gate Current	I _G	10	mA
Drain Current	I _D	20	mA
Allowable Power Dissipation	P _D	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Gate to Drain Breakdown Voltage	V _{(BR)GDS}	I _G = -10μA, V _{DS} = 0	-40			V
Gate Cutoff Current	I _{GSS}	V _{GS} = -20V, V _{DS} = 0			-1.0	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1μA	-0.3	-0.9	-2.0	V
Drain Current	I _{DSS}	V _{DS} = 10V, V _{GS} = 0	※1.2		※12.0	mA
Forward Transfer Admittance	y _{fs}	V _{DS} = 10V, V _{GS} = 0, f = 1kHz	4.5	9.0		mS
Input Capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz		9.0		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz		2.1		pF
Noise Figure	NF	V _{DS} = 10V, R _g = 1kΩ, I _D = 1mA, f = 1kHz		1.5		dB

※: The 2SK1069 is classified by I_{DSS} as follows (unit: mA):

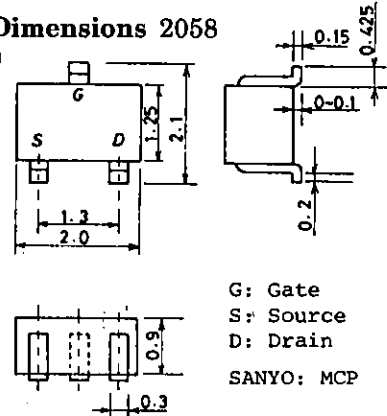
1.2	3	3.0	2.5	4	6.0	5.0	5	12.0
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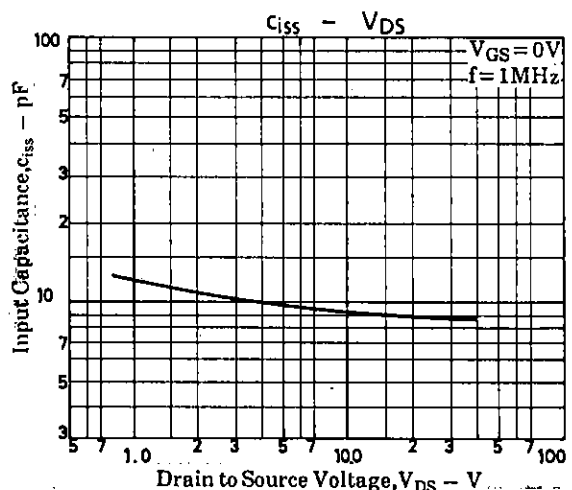
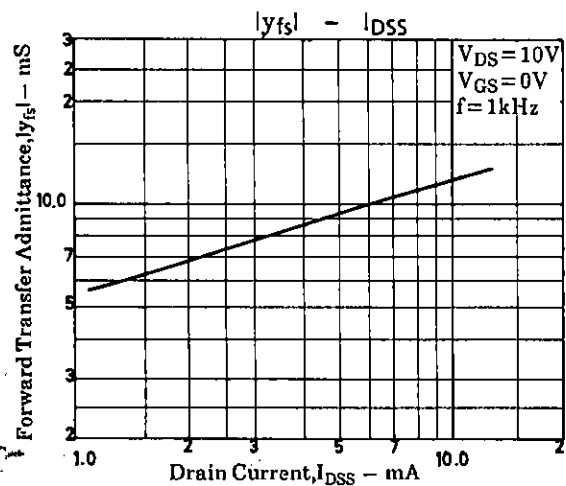
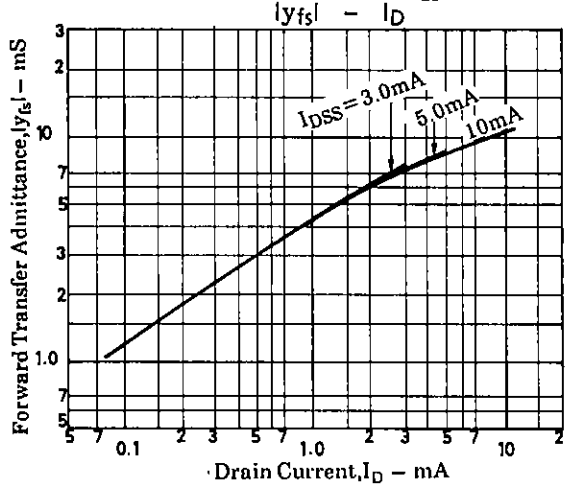
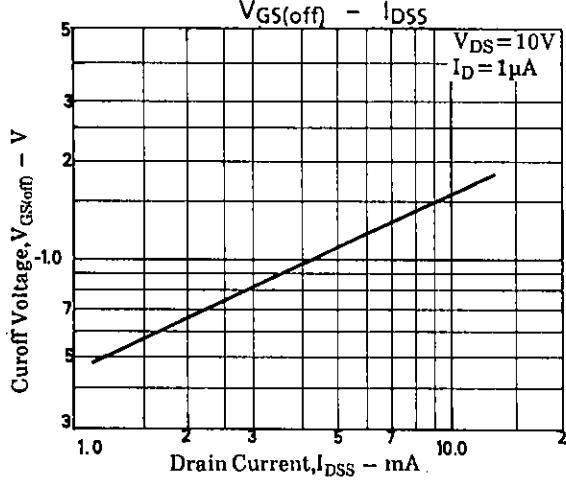
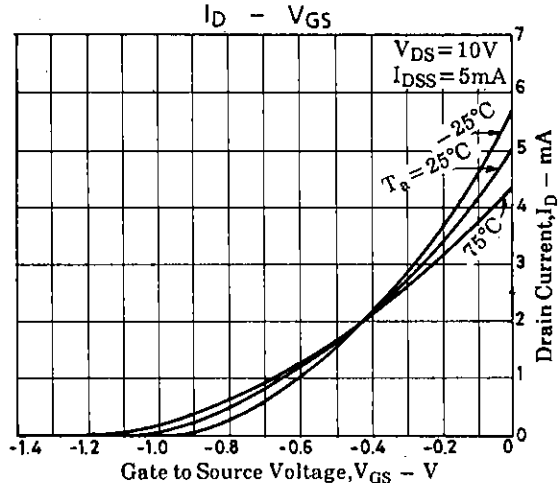
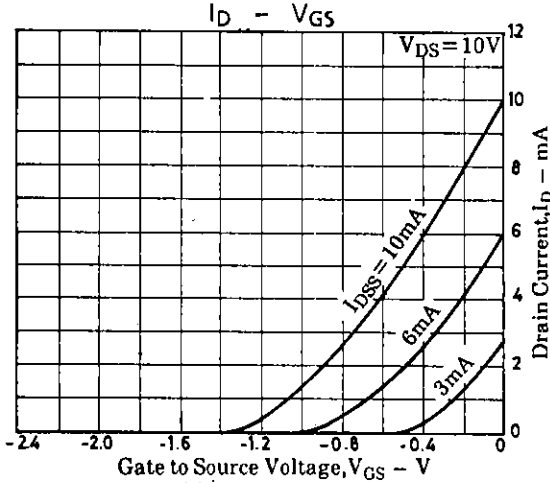
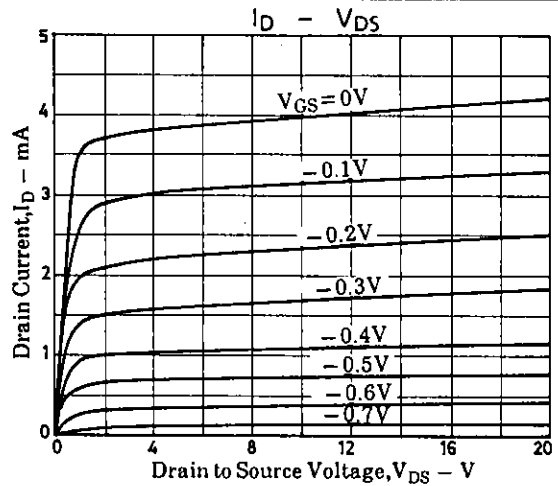
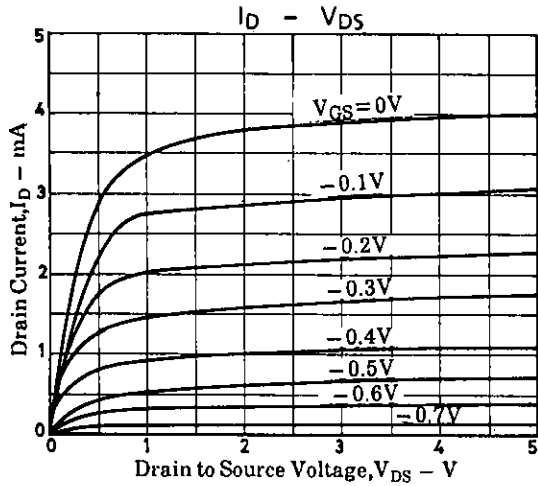
(Note) Marking: FJ

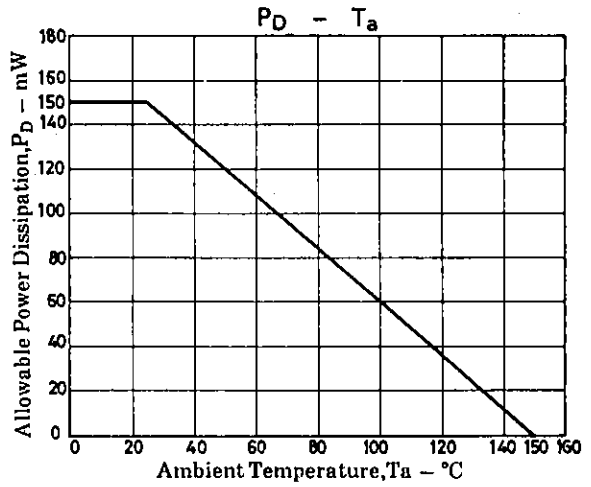
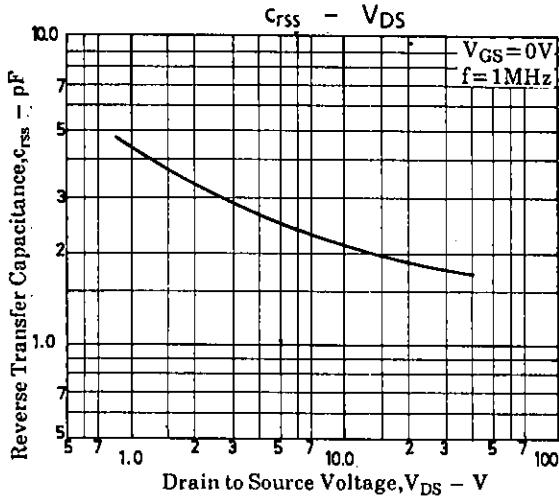
I_{DSS} rank: 3,4,5

●For CP package version, use the 2SK771.

Package Dimensions 2058
(unit: mm)







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